

ABSTRACT

The present invention pertains to forming respective silicides on multiple transistors in a single process. High performance is facilitated with simple and highly integrated process flows. As such, transistors, and an integrated circuit containing the transistors, can be fabricated efficiently and at a low cost. The different silicides can be formed with different materials and/or to different thicknesses. As such, the silicides can have different electrical characteristics, such as resistivity and conductivity. These different attributes instill the transistors with different work functions when formed as gate contacts thereon. This provides an integrated circuit containing the transistors with diverse operating capabilities allowing for the execution of operations requiring more flexibility and/or functionality.